

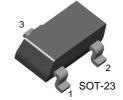
August 2006

## BC846-BC850

### **NPN Epitaxial Silicon Transistor**

#### **Features**

- · Switching and Amplifier Applications
- Suitable for automatic insertion in thick and thin-film circuits
- Low Noise: BC849, BC850
- Complement to BC856 ... BC860



1. Base 2. Emitter 3. Collector

### Absolute Maximum Ratings\* T<sub>a</sub> = 25°C unless otherwise noted

Symbol		Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	: BC846 : BC847/850 : BC848/849	80 50 30	V V V
V <sub>CEO</sub>	Collector-Emitter Voltage	: BC846 : BC847/850 : BC848/849	65 45 30	V V V
V <sub>EBO</sub>	Emitter-Base Voltage	: BC846/847 : BC848/849/850	6 5	V V
I <sub>C</sub>	Collector Current (DC)		100	mA
P <sub>C</sub>	Collector Power Dissipation	on	310	mW
TJ	Junction Temperature		150	°C
T <sub>STG</sub>	Storage Temperature		-65 ~ 150	°C

<sup>\*</sup> These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### Electrical Characteristics\* T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> =30V, I <sub>E</sub> =0			15	nA
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> =5V, I <sub>C</sub> =2mA	110		800	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =0.5mA I <sub>C</sub> =100mA, I <sub>B</sub> =5mA		90 200	250 600	mV mV
V <sub>BE</sub> (sat)	Collector-Base Saturation Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =0.5mA I <sub>C</sub> =100mA, I <sub>B</sub> =5mA		700 900		mV mV
V <sub>BE</sub> (on)	Base-Emitter On Voltage	$V_{CE}$ =5V, $I_{C}$ =2mA $V_{CE}$ =5V, $I_{C}$ =10mA	580	660	700 720	mV mV
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA, f=100MHz		300		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz		3.5	6	pF
C <sub>ib</sub>	Input Capacitance	V <sub>EB</sub> =0.5V, I <sub>C</sub> =0, f=1MHz		9		pF
NF	Noise Figure : BC846/847/848 : BC849/850	$V_{CE}$ = 5V, $I_{C}$ = 200 $\mu$ A $R_{G}$ =2K $\Omega$ , f=1KHz		2 1.2	10 4	dB dB
	: BC849 : BC850	$V_{CE}$ = 5V, $I_{C}$ = 200μA $R_{G}$ =2K $\Omega$ , f=30~15000Hz		1.4 1.4	4 3	dB dB

<sup>\*</sup> Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

# h<sub>FE</sub> Classification

Classification	Α	В	С
h <sub>FE</sub>	110 ~ 220	200 ~ 450	420 ~ 800

#### Ordering Information

Device(note1)	<b>Device Marking</b>	Package	Packing Method	Qty(pcs)	Pin Difinitions
BC846AMTF	8AA	SOT-23	Tape & Reel	3000	1.Base 2.Emitter 3.Collector
BC846BMTF	8AB	SOT-23	Tape & Reel	3000	1.Base 2.Emitter 3.Collector
BC846CMTF	8AC	SOT-23	Tape & Reel	3000	1.Base 2.Emitter 3.Collector
BC847AMTF	8BA	SOT-23	Tape & Reel	3000	1.Base 2.Emitter 3.Collector
BC847BMTF	8BB	SOT-23	Tape & Reel	3000	1.Base 2.Emitter 3.Collector
BC847CMTF	8BC	SOT-23	Tape & Reel	3000	1.Base 2.Emitter 3.Collector
BC848AMTF	8CA	SOT-23	Tape & Reel	3000	1.Base 2.Emitter 3.Collector
BC848BMTF	8CB	SOT-23	Tape & Reel	3000	1.Base 2.Emitter 3.Collector
BC848CMTF	8CC	SOT-23	Tape & Reel	3000	1.Base 2.Emitter 3.Collector
BC849AMTF	8DA	SOT-23	Tape & Reel	3000	1.Base 2.Emitter 3.Collector
BC849BMTF	8DB	SOT-23	Tape & Reel	3000	1.Base 2.Emitter 3.Collector
BC849CMTF	8DC	SOT-23	Tape & Reel	3000	1.Base 2.Emitter 3.Collector
BC850AMTF	8EA	SOT-23	Tape & Reel	3000	1.Base 2.Emitter 3.Collector
BC850BMTF	8EB	SOT-23	Tape & Reel	3000	1.Base 2.Emitter 3.Collector
BC850CMTF	8EC	SOT-23	Tape & Reel	3000	1.Base 2.Emitter 3.Collector

Note1 : Affix "-A,-B,-C" means hFE classification.

Affix "-M" means the matte type package.

Affix "-TF" means the tape & reel type packing.

## **Typical Performance Characteristics**

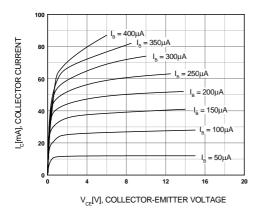


Figure 1. Static Characteristic

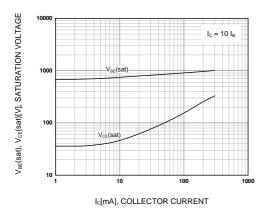


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

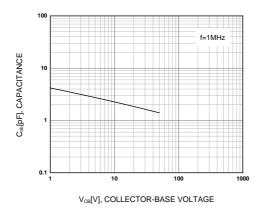


Figure 5. Collector Output Capacitance

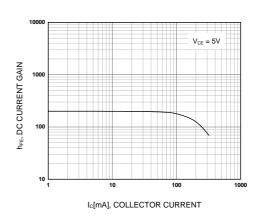


Figure 2. DC current Gain

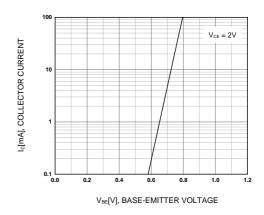


Figure 4. Base-Emitter On Voltage

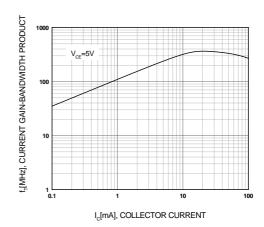
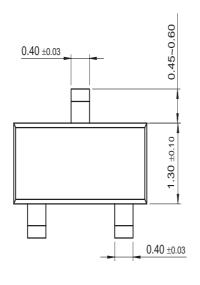


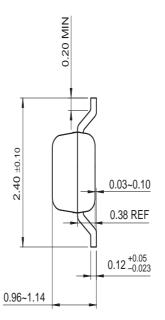
Figure 6. Current Gain Bandwidth Product

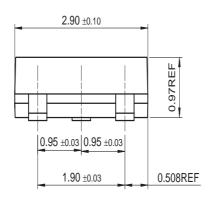
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### **Mechanical Dimensions**

# SOT-23







Dimensions in Millimeters

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